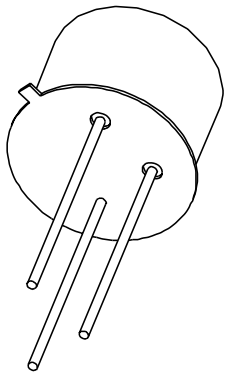


DATA SHEET



2N2219; 2N2219A **NPN switching transistors**

Product specification
Supersedes data of 1997 May 07
File under Discrete Semiconductors, SC04

1997 Sep 03

NPN switching transistors

2N2219; 2N2219A

FEATURES

- High current (max. 800 mA)
- Low voltage (max. 40 V).

APPLICATIONS

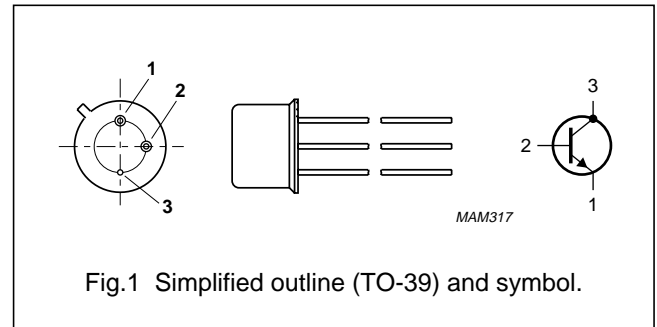
- High-speed switching
- DC and VHF/UHF amplification, for 2N2219 only.

DESCRIPTION

NPN switching transistor in a TO-39 metal package.
PNP complement: 2N2905 and 2N2905A.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector, connected to case



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage 2N2219 2N2219A	open emitter	— —	60 75	V V
V_{CEO}	collector-emitter voltage 2N2219 2N2219A	open base	— —	30 40	V V
I_C	collector current (DC)		—	800	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$	—	800	mW
h_{FE}	DC current gain	$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}$	75	—	
f_T	transition frequency 2N2219 2N2219A	$I_C = 20\text{ mA}; V_{CE} = 20\text{ V}; f = 100\text{ MHz}$	250 300	— —	MHz MHz
t_{off}	turn-off time	$I_{Con} = 150\text{ mA}; I_{Bon} = 15\text{ mA}; I_{Boff} = -15\text{ mA}$	—	250	ns

NPN switching transistors

2N2219; 2N2219A

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	2N2219		–	60	V
	2N2219A		–	75	V
V _{CEO}	collector-emitter voltage	open base	–	30	V
	2N2219A	open base; I _C ≤ 500 mA	–	40	V
V _{EBO}	emitter-base voltage	open collector			
	2N2219		–	5	V
	2N2219A		–	6	V
I _C	collector current (DC)		–	800	mA
I _{CM}	peak collector current		–	800	mA
I _{BM}	peak base current		–	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	–	800	mW
		T _{case} ≤ 25 °C	–	3	W
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	200	°C
T _{amb}	operating ambient temperature		–65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	in free air	190	K/W
R _{th j-c}	thermal resistance from junction to case		50	K/W

NPN switching transistors

2N2219; 2N2219A

CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current 2N2219	$I_E = 0; V_{CB} = 50\text{ V}$	–	10	nA
		$I_E = 0; V_{CB} = 50\text{ V}; T_{amb} = 150\text{ }^{\circ}\text{C}$	–	10	μA
I_{CBO}	collector cut-off current 2N2219A	$I_E = 0; V_{CB} = 60\text{ V}$	–	10	nA
		$I_E = 0; V_{CB} = 60\text{ V}; T_{amb} = 150\text{ }^{\circ}\text{C}$	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 3\text{ V}$	–	10	nA
h_{FE}	DC current gain	$I_C = 0.1\text{ mA}; V_{CE} = 10\text{ V}$	35	–	
h_{FE}	DC current gain	$I_C = 1\text{ mA}; V_{CE} = 10\text{ V}$	50	–	
h_{FE}	DC current gain	$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}$	75	–	
h_{FE}	DC current gain 2N2219A	$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; T_{amb} = -55\text{ }^{\circ}\text{C}$	35	–	
h_{FE}	DC current gain	$I_C = 150\text{ mA}; V_{CE} = 1\text{ V}; \text{note 1}$	50	–	
h_{FE}	DC current gain	$I_C = 150\text{ mA}; V_{CE} = 10\text{ V}; \text{note 1}$	100	300	
h_{FE}	DC current gain 2N2219 2N2219A	$I_C = 500\text{ mA}; V_{CE} = 10\text{ V}; \text{note 1}$	30	–	
			40	–	
V_{CEsat}	collector-emitter saturation voltage 2N2219 2N2219A	$I_C = 150\text{ mA}; I_B = 15\text{ mA}; \text{note 1}$	–	400	mV
			–	300	mV
V_{CEsat}	collector-emitter saturation voltage 2N2219 2N2219A	$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	1.6	V
			–	1	V
V_{BEsat}	base-emitter saturation voltage 2N2219 2N2219A	$I_C = 150\text{ mA}; I_B = 15\text{ mA}; \text{note 1}$	–	1.3	V
			0.6	1.2	V
V_{BEsat}	base-emitter saturation voltage 2N2219 2N2219A	$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	2.6	V
			–	2	V
C_c	collector capacitance	$I_E = I_e = 0; V_{CB} = 10\text{ V}$	–	8	pF
C_e	emitter capacitance 2N2219A	$I_C = I_c = 0; V_{EB} = 500\text{ mV}$	–	25	pF
f_T	transition frequency 2N2219 2N2219A	$I_C = 20\text{ mA}; V_{CE} = 20\text{ V}; f = 100\text{ MHz};$	250	–	MHz
			300	–	MHz
F	noise figure 2N2219A	$I_C = 0.2\text{ mA}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	–	4	dB

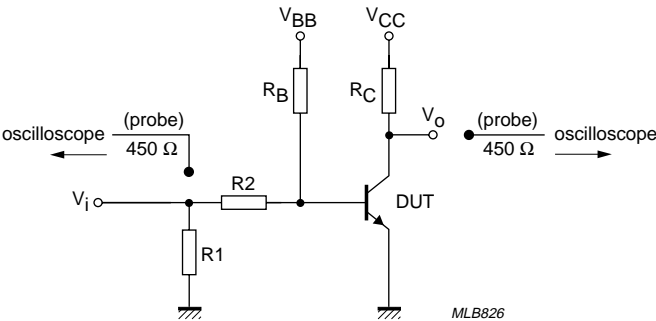
NPN switching transistors

2N2219; 2N2219A

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Switching times (between 10% and 90% levels) for type 2N2219A; see Fig.2					
t _{on}	turn-on time	I _C on = 150 mA; I _B on = 15 mA; I _B off = -15 mA	—	35	ns
t _d	delay time		—	15	ns
t _r	rise time		—	20	ns
t _{off}	turn-off time		—	250	ns
t _s	storage time		—	200	ns
t _f	fall time		—	60	ns

Note

1. Pulse test: t_p ≤ 300 μs; δ ≤ 0.02.



V_i = 9.5 V; T = 500 μs; t_p = 10 μs; t_r = t_f ≤ 3 ns.
R₁ = 68 Ω; R₂ = 325 Ω; R_B = 325 Ω; R_C = 160 Ω.
V_{BB} = -3.5 V; V_{CC} = 29.5 V.
Oscilloscope: input impedance Z_i = 50 Ω.

Fig.2 Test circuit for switching times.

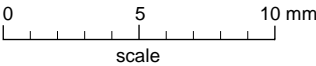
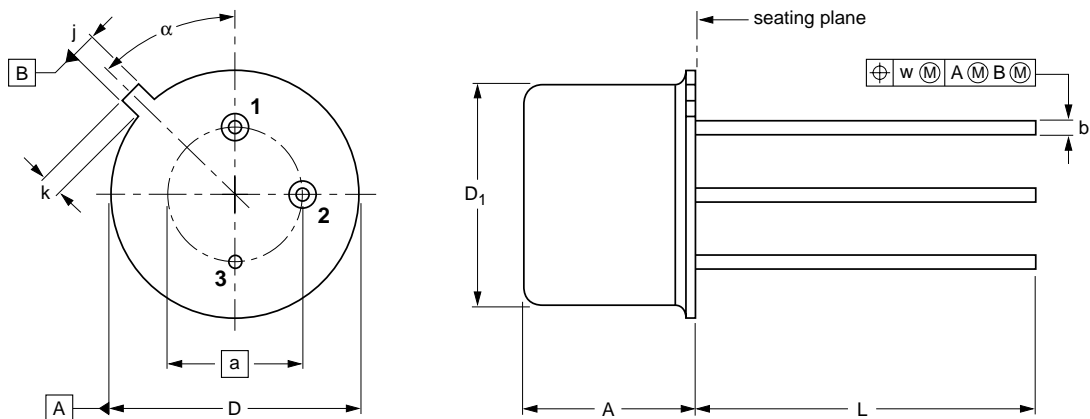
NPN switching transistors

2N2219; 2N2219A

PACKAGE OUTLINE

Metal-can cylindrical single-ended package; 3 leads

SOT5/11



DIMENSIONS (mm are the original dimensions)

UNIT	A	a	b	D	D ₁	j	k	L	w	α
mm	6.60 6.35	5.08	0.48 0.41	9.39 9.08	8.33 8.18	0.85 0.75	0.95 0.75	14.2 12.7	0.2	45°

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT5/11		TO-39				97-04-11

NPN switching transistors2N2219; 2N2219A

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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